

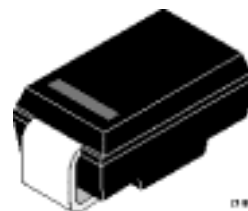


Schottky Diode (FH1N5818)

肖特基二极管

Features 特征:

- Ideal for surface mounted applications
 - Low leakage current.
 - For use in low voltage, high frequency inverters free wheeling, and polarity protection applications.
- DO-214AC



1.0Ampere Schottky Barrier Rectifiers

1.0 安培肖特基势垒整流二极管

Absolute Maximum Ratings* 最大绝对值

T_A=25 unless otherwise noted

Symbol 符号	Parameter 参数	Value	Unites
I _{F(AV)}	Average Rectified Current 平均整流电流	1.0	A
I _{FSM}	Non-repetitive Peak Forward Surge Current 无重复正向峰值浪涌电流 8.3 ms single half-sine-wave superimposed on rated load	30	A
P _D	Total Device Dissipation 总耗散功率 Derate above 25	1.25 12.5	W MW/
R _{JA}	Thermal Resistance, Junction to Ambient 热阻	20	/W
T _{STG}	Storage Temperature Range 储存温度	-65 to +150	
T _J	Operating Junction Temperature 工作结温	-65 to +150	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

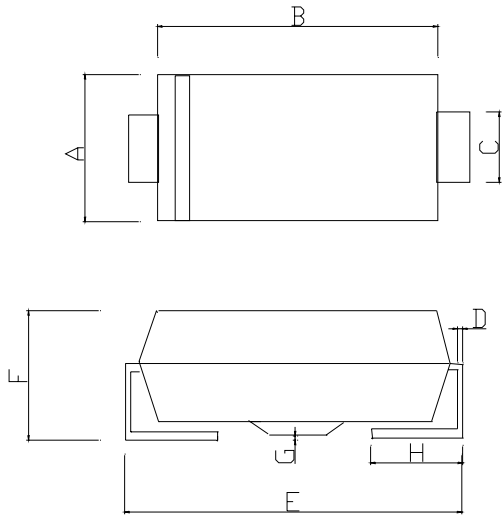
Electrical Characteristics T_A=25 unless otherwise noted

Symbol 符号	Parameter 参数	Value	Units
V _{RRM}	Maximum Peak Repetitive Reverse Voltage 最大峰值反向电压	30	V
V _{RMS}	Maximum RMS Voltage	21	V
V _R	DC Reverse Voltage (Rated V _R)反向电压	30	V
I _{RM}	Maximum Instantaneous Reverse Current 最大瞬间反向电流 T _A =25 @rated V _R T _A =100	0.5 10	mA mA
V _{FM}	Maximum Instantaneous Forward Voltage 最大瞬间正向电压 @1.0A	500	mV
C	Typical Junction capacitance 典型结容	110	pF



DO-214AC Dimensions in INCHES(MILLIMETERS)

DO - 214AC 尺寸 英寸 (毫米)



	A	B	C	D
MAX	0.110(2.79)	0.177(4.50)	0.075(1.90)	0.012(0.305)
MIN	0.100(2.54)	0.157(3.99)	0.052(1.32)	0.006(0.152)
	E	F	G	H
MAX	0.208(5.28)	0.90(2.29)	0.008(0.203)	0.060(1.52)
MIN	0.194(4.93)	0.078(1.98)	0.004(0.102)	0.030(0.76)